

2N3724, 2N3725 — 2N4013, 2N4014 (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS (continued)

Collector-Emitter Saturation Voltage* ($I_C = 10 \text{ mA dc}, I_B = 1.0 \text{ mA dc}$)	2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014	$V_{CE(sat)}$ *	-	0.25	Vdc
($I_C = 100 \text{ mA dc}, I_B = 10 \text{ mA dc}$)			-	0.20	
($I_C = 300 \text{ mA dc}, I_B = 30 \text{ mA dc}$)			-	0.26	
($I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$)			-	0.32	
($I_C = 800 \text{ mA dc}, I_B = 80 \text{ mA dc}$)			-	0.40	
($I_C = 1.0 \text{ A dc}, I_B = 100 \text{ mA dc}$)			-	0.42	
($I_C = 1.0 \text{ A dc}, I_B = 100 \text{ mA dc}$)			-	0.52	
Base-Emitter Saturation Voltage* ($I_C = 10 \text{ mA dc}, I_B = 1.0 \text{ mA dc}$)	2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014 2N3724, 2N4013 2N3725, 2N4014	$V_{BE(sat)}$ *	-	0.76	Vdc
($I_C = 100 \text{ mA dc}, I_B = 10 \text{ mA dc}$)			-	0.86	
($I_C = 300 \text{ mA dc}, I_B = 30 \text{ mA dc}$)			-	1.1	
($I_C = 500 \text{ mA dc}, I_B = 50 \text{ mA dc}$)			0.9	1.2	
($I_C = 800 \text{ mA dc}, I_B = 80 \text{ mA dc}$)			-	1.5	
($I_C = 1.0 \text{ A dc}, I_B = 100 \text{ mA dc}$)			-	1.7	
($I_C = 1.0 \text{ A dc}, I_B = 100 \text{ mA dc}$)			-	0.95	

SMALL-SIGNAL CHARACTERISTICS

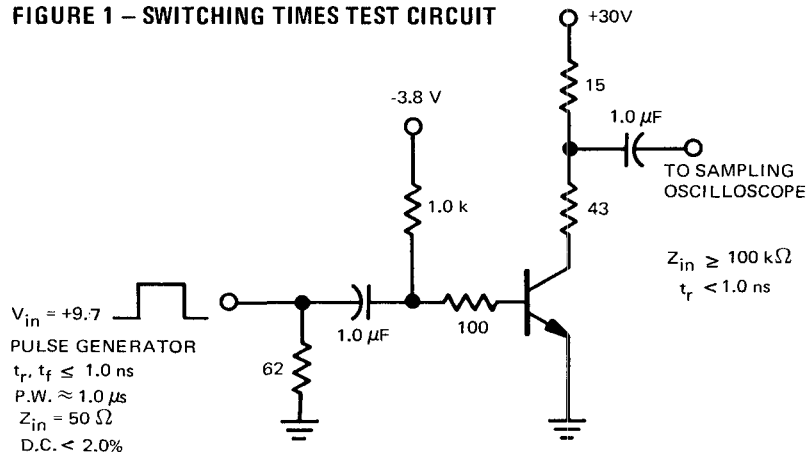
Current-Gain-Bandwidth Product ($I_C = 50 \text{ mA dc}, V_{CE} = 10 \text{ V dc}, f = 100 \text{ MHz}$)	f_T	300	-	MHz
Output Capacitance ($V_{CB} = 10 \text{ V dc}, I_E = 0, f = 140 \text{ kHz}$)	C_{ob}	-	12	pF
		-	10	
Input Capacitance ($V_{BE} = 0.5 \text{ V dc}, I_C = 0, f = 140 \text{ kHz}$)	C_{ib}	-	55	pF

SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = 30 \text{ V dc}, V_{BE(off)} = 3.8 \text{ V dc}, I_C = 500 \text{ mA dc}, I_{B1} = 50 \text{ mA dc})$ (See Figure 1)	t_{on}	-	35	ns
Delay Time		t_d	-	10	ns
Rise Time		t_r	-	30	ns
Turn-Off Time	$(V_{CC} = 30 \text{ V dc}, I_C = 500 \text{ mA dc}, I_{B1} = I_{B2} = 50 \text{ mA dc})$ (See Figure 1)	t_{off}	-	60	ns
Storage Time		t_s	-	50	ns
Fall Time		t_f	-	25	ns
				30	ns

* Pulse Test: Pulse Width = 300 μs , Duty Cycle = 1.0%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT



RF POWER TRANSISTORS

(Listed in order of operating test frequency and power output)

ALL SILICON NPN

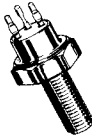
Type	f MHz	P _{out} W	@	P _{in} W
2N3295	30	0.3		0.012
2N3296	30	3.0		0.075
2N3297	30	12		1.2
2N2948	30	15		2.0
2N2951, 52	50	0.6		0.1
2N2949, 50	50	3.5		0.35
2N2947	50	15		2.0
2N3950	50	50		4.5
2N3298	80	0.1		-
2N3375	100	7.5		1.0
2N3818	100	15		3.0
2N3553	175	2.5		0.25
2N3961	175	4.0		0.5
2N3924	175	4.0		1.0
2N3925	175	5.0		1.3
2N3926	175	7.0		2.0
2N3927	175	12		4.0
2N3632	175	13.5		3.5
2N3137	250	0.7		0.1
2N3664	250	2.2		0.4
2N3866	400	1.0		0.1
2N3948	400	1.0		0.25
2N4012	400	3.0 (typ)		1.0
2N3375	400	3.0 (min)		1.0
2N3733	400	10		4.0

HIGH-VOLTAGE TRANSISTORS

Type	V _{CEO}	f _T (MHz)		@	I _C mA
		min	max		
2N4924	100	100	500		20
2N4925	150	100	500		20
2N4926	200	30	300		10
2N4927	250	30	300		10

2N3818 (SILICON)

$G_{PE} = 7 \text{ dB @ 100 MHz typ}$
 $P_{out} = 15 \text{ W @ 100 MHz}$



NPN silicon annular transistor for high-frequency power applications to 150 MHz.

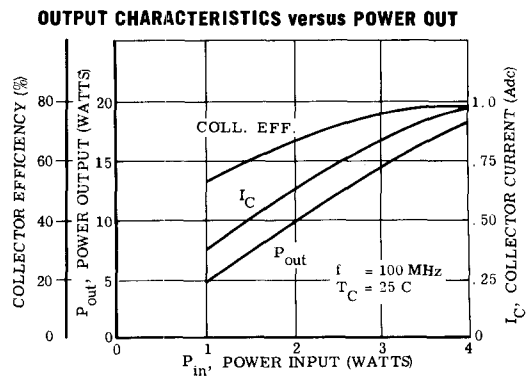
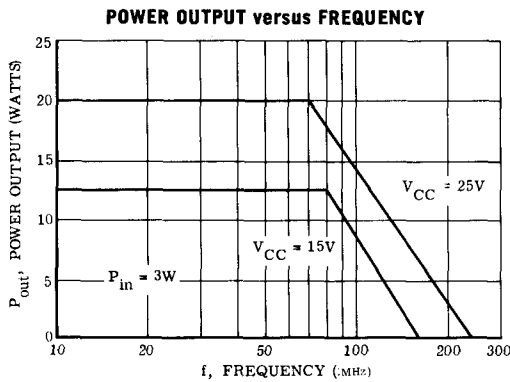
All leads isolated from case

CASE 36 (TO-60)

MAXIMUM RATINGS *

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CB}	60	Vdc
Collector-Emitter Voltage	V_{CES}	60	Vdc
Emitter-Base Voltage	V_{EB}	4	Vdc
Collector-Current (continuous)	I_C	2.0	Adc
Base-Current (continuous)	I_B	1.0	mAdc
Power Input (Nominal)	P_{in}	5.0	Watts
Power Output (Nominal)	P_{out}	20.0	Watts
Total Device Dissipation @ 25°C Case Temperature	P_D	25.0	Watts
Derating Factor above 25°C		167	mW/°C
Junction Temperature	T_J	175	°C
Storage Temperature	T_{stg}	-65 to +175	°C

* The maximum ratings as given for dc conditions can be exceeded on a pulse basis. See electrical characteristics.



2N3818 (continued)

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Sustain Voltage $I_C = 0.25 \text{ Adc}, R_{BE} = 0$	$V_{CES(sus)}^*$	80	100	--	Vdc
Collector-Emitter-Open Base Sustain Voltage $I_C = 0.25 \text{ Adc}, I_B = 0$	$V_{CEO(sus)}^*$	40	--	--	Vdc
Collector-Emitter Current $V_{CE} = 60 \text{ Vdc}, V_{BE} = 0$ $V_{CE} = 50 \text{ Vdc}, V_{BE} = 0, T_C = 175^\circ\text{C}$	I_{CES}	--	--	0.5 1.0	mAdc
Collector Cutoff Current $V_{CB} = 50 \text{ Vdc}, I_E = 0$	I_{CBO}	--	--	1	μAdc
Emitter Cutoff Current $V_{EB} = 4 \text{ Vdc}, I_C = 0$	I_{EBO}	--	--	100	μAdc
DC Current Gain $I_C = 400 \text{ mAdc}, V_{CE} = 2 \text{ Vdc}$ $I_C = 1 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$	h_{FE}	5.0 5.0	--	50 --	
Collector-Emitter Saturation Voltage $I_C = 1.0 \text{ Adc}, I_B = 250 \text{ mAdc}$	$V_{CE(sat)}$	--	--	0.5	Vdc
Base-Emitter Saturation Voltage $I_C = 1.0 \text{ Adc}, I_B = 250 \text{ mAdc}$	$V_{BE(sat)}$	--	--	2.0	Vdc
AC Current Gain $V_{CE} = 2.0 \text{ Vdc}, I_C = 400 \text{ mAdc},$ $f = 50 \text{ mc}$	$ h_{fe} $	3	--	--	
Collector Output Capacitance $V_{CB} = 25 \text{ Vdc}, I_E = 0, f = 100 \text{ kHz}$	C_{ob}	--	--	40	pF
Power Input $P_{out} = 15 \text{ W}, f = 100 \text{ MHz}$	P_{in}	--	3.0	3.75	Watts
Efficiency $V_{CE} = 25 \text{ Vdc}$ $I_{C(max.)} = 1 \text{ Adc}$	η	60	70	--	%

*Pulse Measurement: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle = 2%.

